
HRW26F

Silicon Schottky Barrier Diode for High Frequency Rectifying

HITACHI

ADE-208-156B (Z)

Rev. 2

Nov. 1994

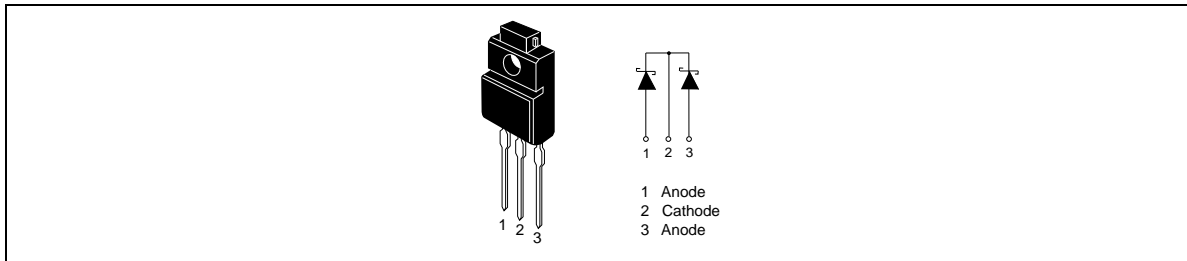
Features

- Low forward voltage drop. ($V_F = 0.55V$ max)
- High reverse voltage. ($V_R = 40V$ max)
- Full molded fin enables easy insulation from heat sink.

Ordering Information

Type No.	Laser Mark	Package Code
HRW26F	HRW26F	TO-220FM

Pin Arrangement



HRW26F

Absolute Maximum Ratings (Ta = 25°C)*1

Item	Symbol	Value	Unit
Repetitive peak reverse voltage	V_{RRM}	40	V
Average forward current	I_O^{*2}	10	A
Non-Repetitive peak forward surge current	I_{FSM}^{*3}	70	A
Junction temperature	Tj	125	°C
Storage temperature	Tstg	-40 to +125	°C

- Notes: 1. Per one device
 2. Square wave, Duty (1/2), Tc = 95°C, Sum of two devices
 3. Half sine wave 10msec

Electrical Characteristics (Ta = 25°C)*

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	V_F	—	—	0.55	V	$I_F = 4.0A$
Reverse current	I_R	—	—	1.0	mA	$V_R = 40V$

Note: Per one device

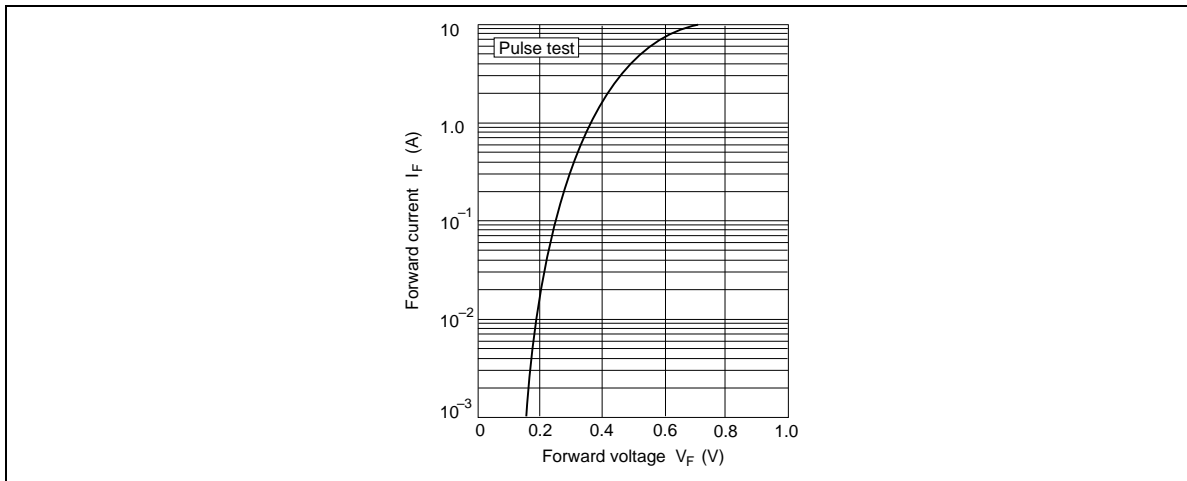


Fig.1 Forward current Vs. Forward voltage

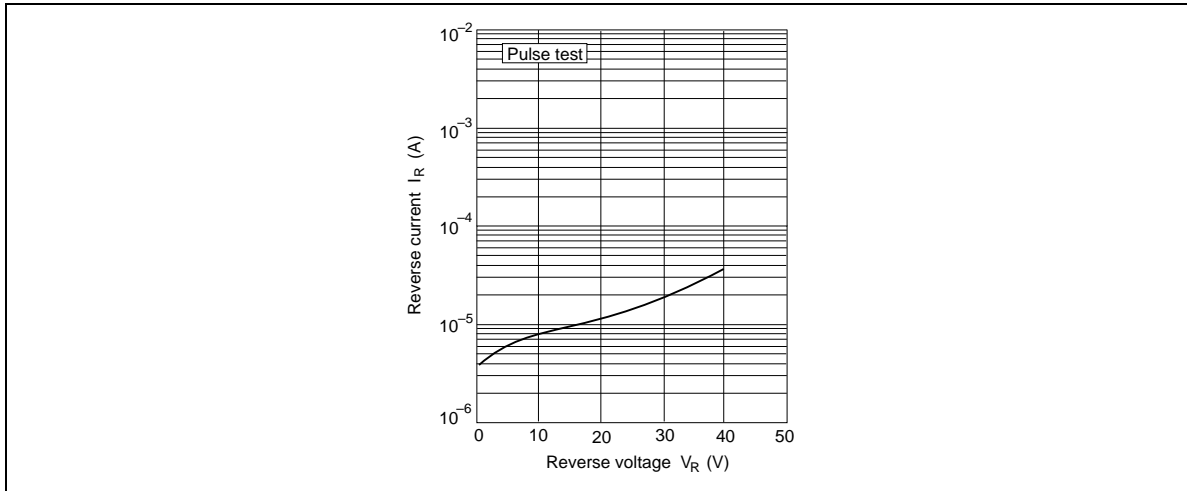


Fig.2 Reverse current Vs. Reverse voltage

Package Dimensions

